



# GUVB-S11SD



## TECHNICAL DATA

### UV-B Sensor

#### Features

- Aluminium Gallium Nitride Based Material
- Schottky-type Photodiode
- Photovoltaic Mode Operation
- Good Visible Blindness
- High Responsivity & Low Dark Current

#### Applications

- UV Index Monitoring
- UV-B Lamp Monitoring

#### Absolute Maximum Ratings

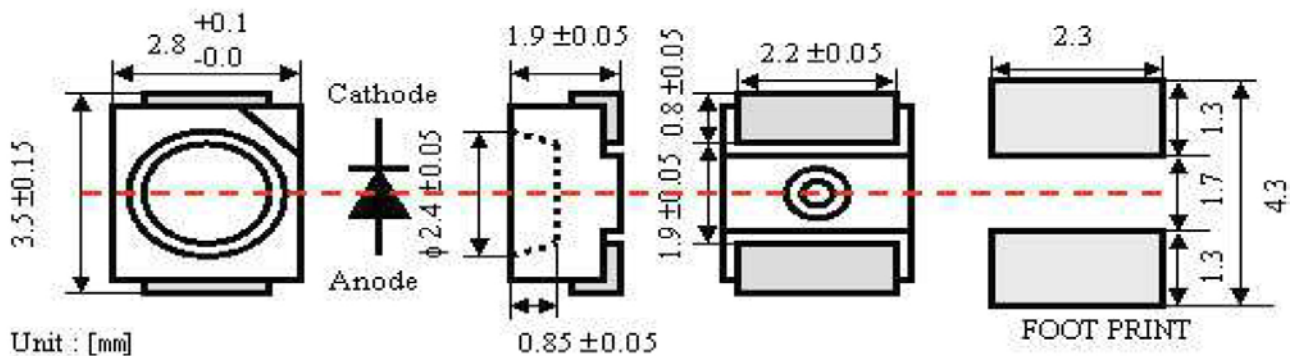
Item	Symbol	Value	Unit
Forward Current	$I_F$	1	mA
Reverse Voltage	$V_R$	3	V
Operating Temperature	$T_{op}$	-30 ... +85	°C
Storage Temperature	$T_{st}$	-40 ... +90	°C
Soldering Temperature *	$T_{sol}$	260	°C

\* must be completed within 10 seconds

#### Characteristics (25°C)

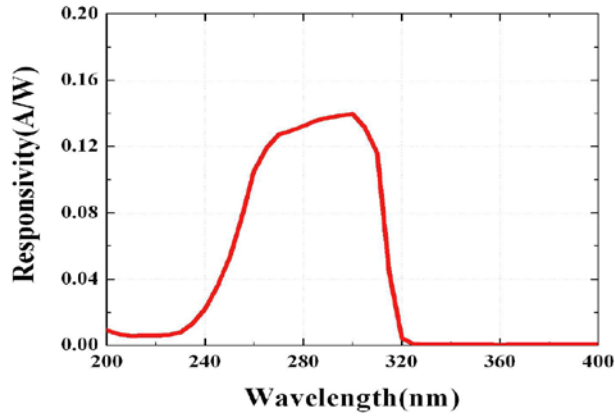
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Dark Current	$I_D$	$V_R = 0.1 V$	-	-	1	nA
Photo Current	$I_{PD}$	UVB Lamp, 1 mW/cm <sup>2</sup>	-	69	-	nA
		1 UVI	-	1.4	-	nA
Temperature Coefficient	$I_{TC}$	UVB Lamp	-	0.1	-	% / °C
Responsivity	R	$\lambda = 300 nm, V_R = 0 V$	-	0.14	-	A/W
Spectral Detection Range	$\lambda$	10% of R	235	-	320	nm

#### Package Dimension





## Responsivity Curve



## Photocurrent along UV Power

